



DMN6069SFG

60V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	50mΩ @ V _{GS} = 10V	18A
	$63m\Omega @ V_{GS} = 4.5V$	16A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

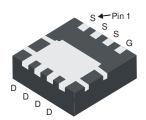
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products (PowerDI[®])
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (\$\sqrt{2}\$)
- Weight: 0.03 grams (Approximate)

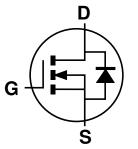


Bottom View



PowerDI3333-8

Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6069SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMN6069SFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N69 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Dusin Comment (Note C) // 10//	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	5.6 4.5	А
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	18 14.5	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	I _{DM}	25	Α		
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2.5	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	12	Α
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	7.2	mJ		

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_{D}	0.93	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	134	°C/W
L Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	82	C/VV
Total Power Dissipation (Note 6)		P_{D}	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	53	°C/W
L Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R _{0JA}	33	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	5		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)	I _{DSS}	_	_	100	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS}=\pm 20V,V_{DS}=0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Dagger	_	39	50	mΩ	$V_{GS} = 10V, I_D = 4.5A$	
Static Drain-Source On-Hesistance	R _{DS(ON)}	_	47	63	11122	$V_{GS} = 4.5V, I_D = 3A$	
Diode Forward Voltage	V_{SD}	_	_	1.1	V	$V_{GS} = 0V, I_S = 2.5A$	
On State Drain Current (Note 9)	$I_{D(ON)}$	20	_	_	Α	$V_{DS} \ge 5V$, $V_{GS} = 10V$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	CISS	_	740	1,480	pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Output Capacitance	Coss	_	40	80	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{RSS}	_	28	55	pF	1 = 1.0WH2	
Gate Resistance	R _G	_	2.2	4	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	_	6.4	12	nC		
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	14	25	nC	V 20V I 10A	
Gate-Source Charge	Q _{GS}	_	2.8	5.5	nC	$V_{DS} = 30V, I_D = 12A$	
Gate-Drain Charge	Q _{GD}	_	2.3	5	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	3.6	10	ns		
Turn-On Rise Time	t _R	_	5.0	10	ns	$V_{DS} = 30V, I_D = 12A$	
Turn-Off Delay Time	t _{D(OFF)}	_	12	24	ns	$V_{GS} = 10V, R_G = 6.0\Omega$	
Turn-Off Fall Time	t _F	_	3.3	10	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	11	22	ns	1 4 5 A divide 100 A (v.s.	
Body Diode Reverse Recovery Charge	Q_{RR}	_	5.1	10	nC	$I_F = 4.5A$, di/dt = 100A/ μ s	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

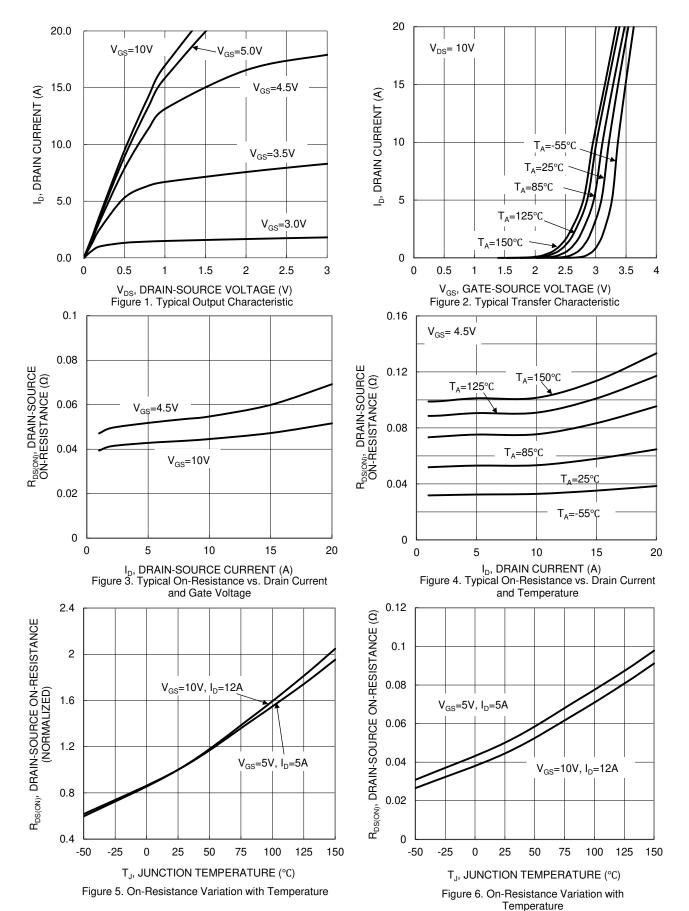
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25$ °C.

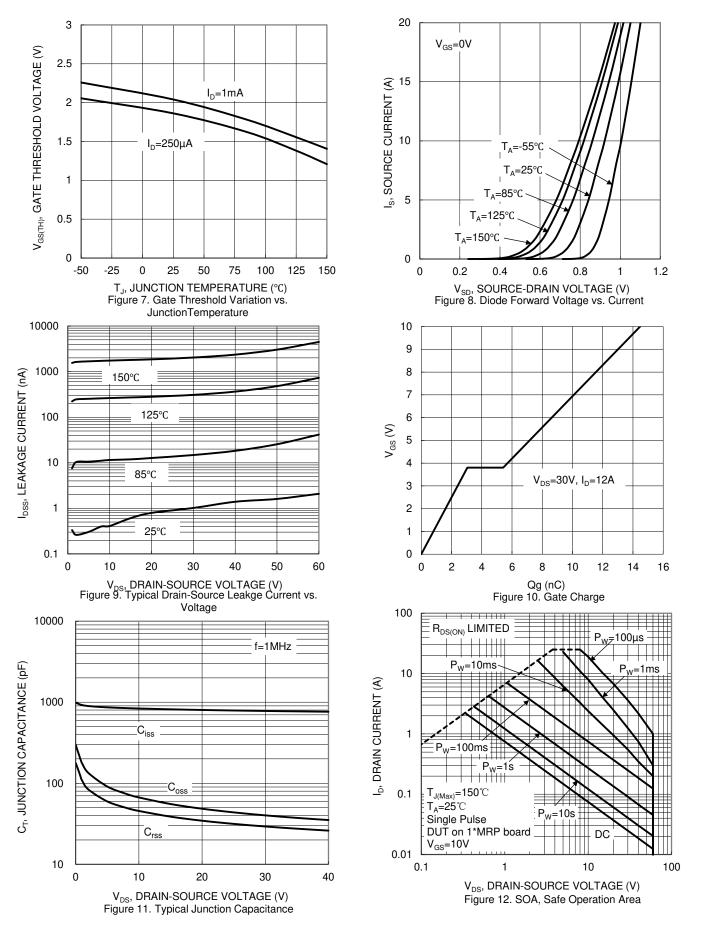
^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.

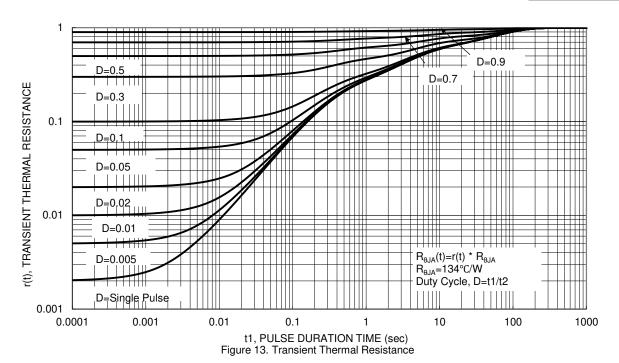










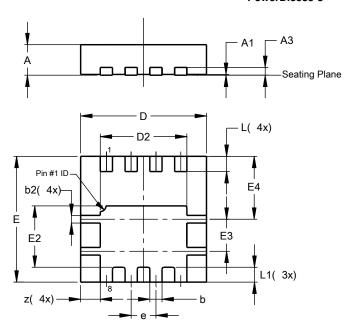




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

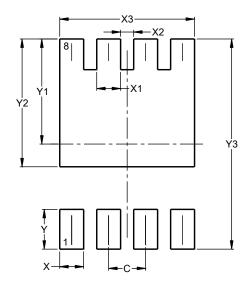


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A 3	-	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
E	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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